

ROITHNER LASERTECHNIK

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S6520MG TECHNICAL DATA



High Power Visible Wavelength Laserdiode

Structure **InGaAlP**, index guided single transverse mode

Lasing wavelength **655 nm typ.**

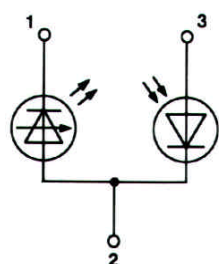
Output power **20 mW, CW**

Package **5.6 mm, TO-18**

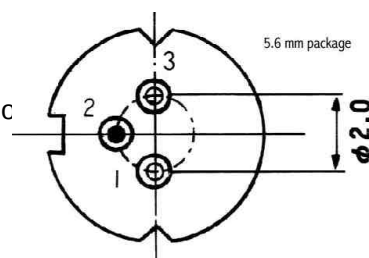


NOTE!
 LASERDIODE
 MUST BE COOLED!

PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Maximum Ratings (T_c = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P _o	20	mW
LD Reverse Voltage	V _{R(LD)}	2	V
PD Reverse Voltage	V _{R(PD)}	30	V
Operation Case Temperature	T _c	-10 .. +60	°C
Storage Temperature	T _{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (T_c = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold Current	I _{th}			15	20	mA
Operation Current	I _{op}	P _o = 20 mW		35	45	mA
Operating Voltage	V _{op}	P _o = 20 mW		2.3	2.8	V
Lasing Wavelength	λ _p	P _o = 20 mW	650	657	664	nm
Beam Divergence	θ	P _o = 20 mW	5	7	9	°
Beam Divergence	θ _⊥	P _o = 20 mW	30	32	38	°
Slope Efficiency	η		0.5	0.7	1	mW/mA
Monitor Current	I _m	P _o = 20 mW	50	200	500	μA